

FDS3672-VB Datasheet

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY

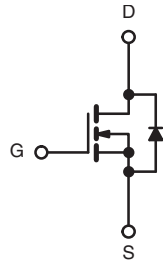
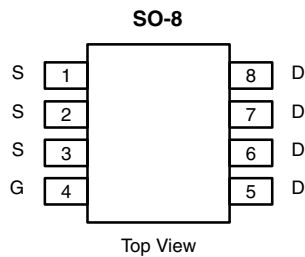
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^a	Q _g (Typ.)
100	0.0090 at V _{GS} = 10 V	16	27.9 nC
	0.0105 at V _{GS} = 7.5 V	15.2	
	0.0110 at V _{GS} = 6.0 V	14	

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:

APPLICATIONS

- DC/DC Primary Side Switch
- Telecom/Server
- Motor Drive Control
- Synchronous Rectification


RoHS
 COMPLIANT


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	16	A
	T _C = 70 °C	13	
	T _A = 25 °C	10.2 ^{b, c}	
	T _A = 70 °C	7.4 ^{b, c}	
Pulsed Drain Current (t = 300 μs)	I _{DM}	70	
Continuous Source-Drain Diode Current	T _C = 25 °C	7	
	T _A = 25 °C	3.1 ^{b, c}	
Single Pulse Avalanche Current	I _{AS}	30	
Avalanche Energy	E _{AS}	45	mJ
Maximum Power Dissipation	T _C = 25 °C	7.8	W
	T _C = 70 °C	5	
	T _A = 25 °C	3.5 ^{b, c}	
	T _A = 70 °C	2.2 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	29	35	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	13	16	

Notes:

a. Based on T_C = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under steady state conditions is 80 °C/W.

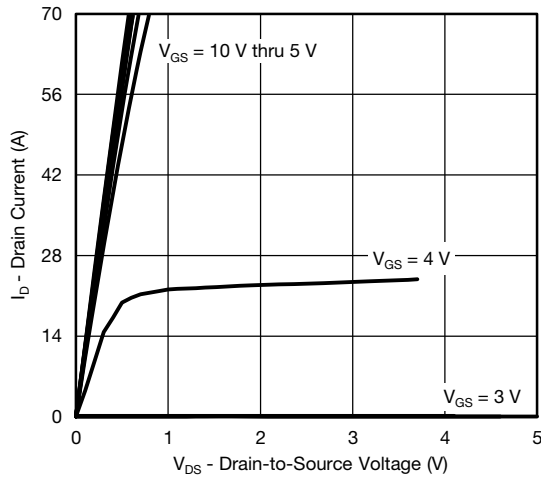
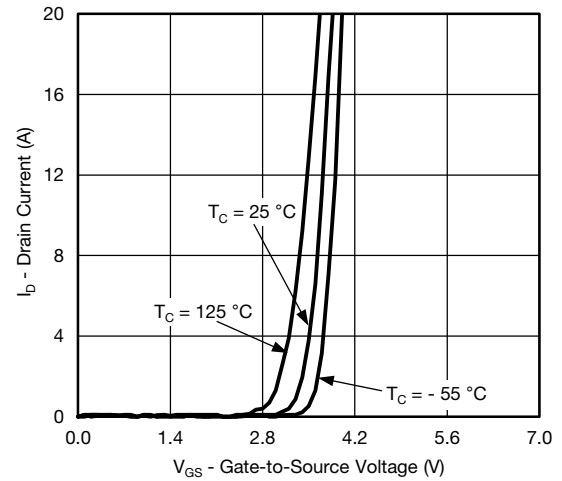
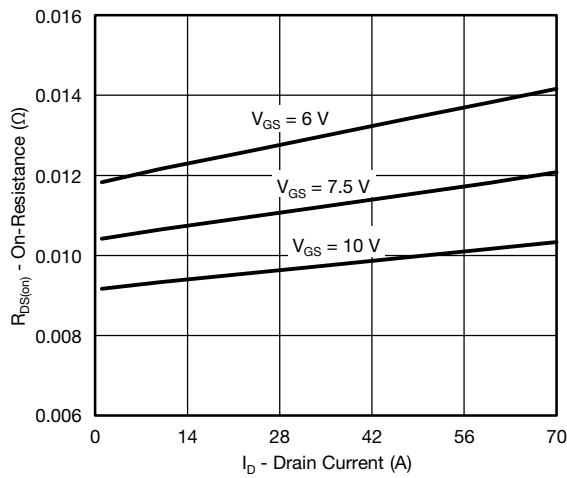
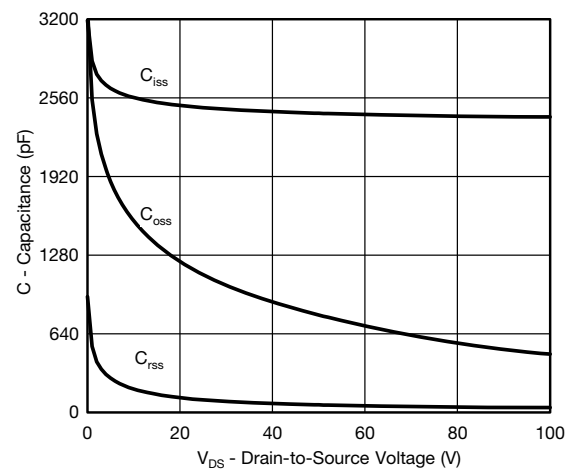
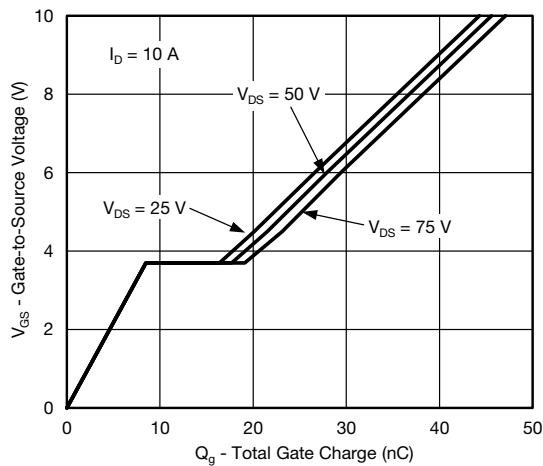
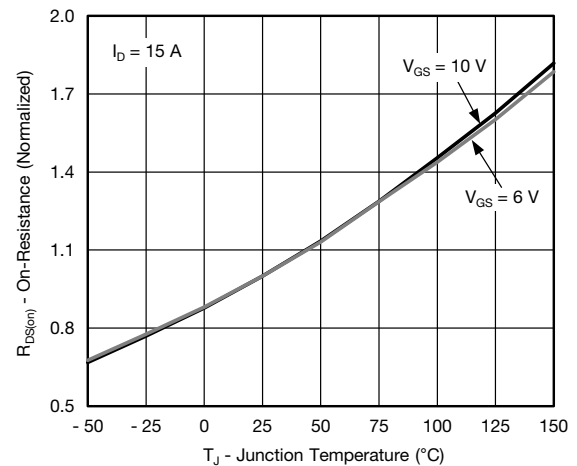
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		67		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6.4		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A		0.0090		Ω
		V _{GS} = 7.5 V, I _D = 12 A		0.0105		
		V _{GS} = 6.0 V, I _D = 10 A		0.0110		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A		54		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		3410		pF
Output Capacitance	C _{oss}			790		
Reverse Transfer Capacitance	C _{rss}			160		
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 10 A		45.6	69	nC
		V _{DS} = 50 V, V _{GS} = 6 V, I _D = 10 A		27.9	42	
Gate-Source Charge	Q _{gs}			8.5		
Gate-Drain Charge	Q _{gd}			9.2		
Output Charge	Q _{oss}	V _{DS} = 50 V, V _{GS} = 0 V		63	95	
Gate Resistance	R _g	f = 1 MHz	0.4	1.3	2.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 5 Ω I _D ≅ 10 A, V _{GEN} = 7.5 V, R _g = 1 Ω		16	32	ns
Rise Time	t _r			11	22	
Turn-Off Delay Time	t _{d(off)}			35	70	
Fall Time	t _f			10	20	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		14	28	
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			36	70	
Fall Time	t _f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			7	A
Pulse Diode Forward Current ^a	I _{SM}				70	
Body Diode Voltage	V _{SD}	I _S = 5 A		0.75	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C		49	95	ns
Body Diode Reverse Recovery Charge	Q _{rr}			58	115	nC
Reverse Recovery Fall Time	t _a			21		ns
Reverse Recovery Rise Time	t _b			28		

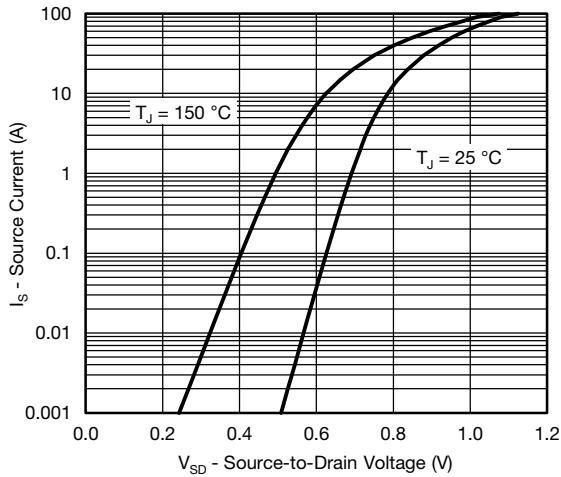
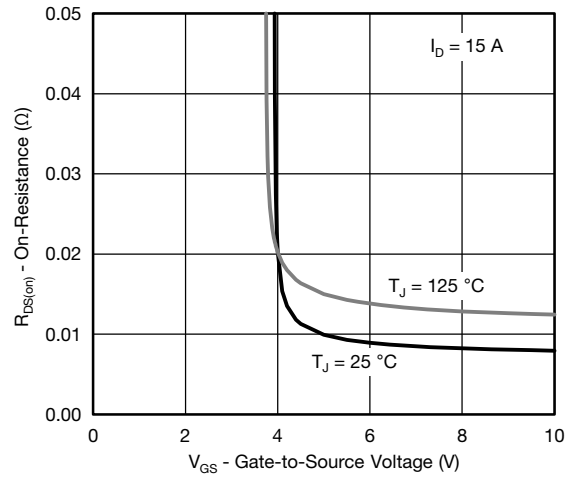
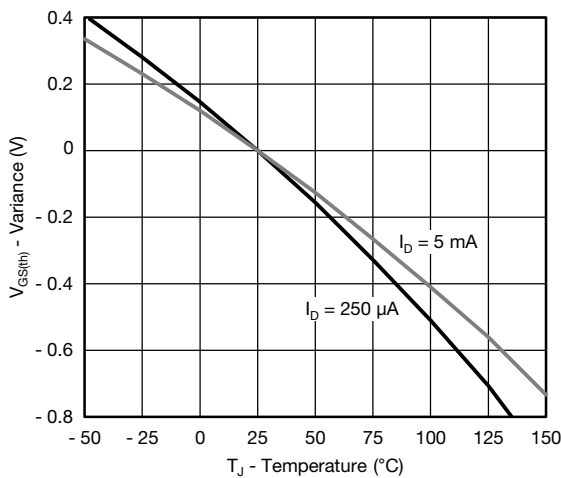
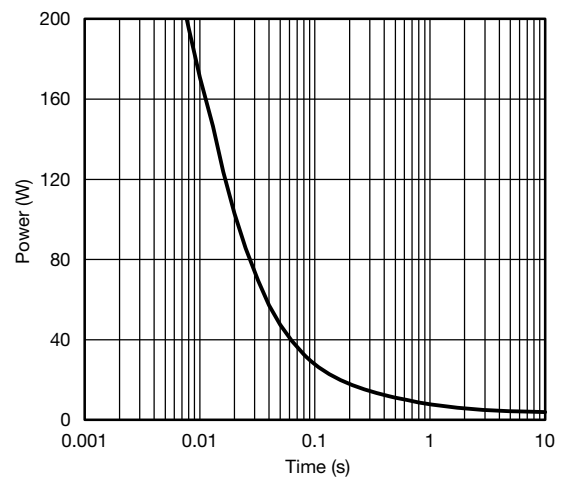
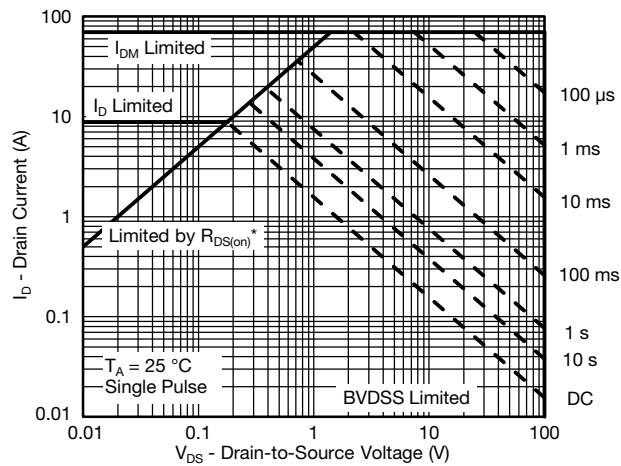
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

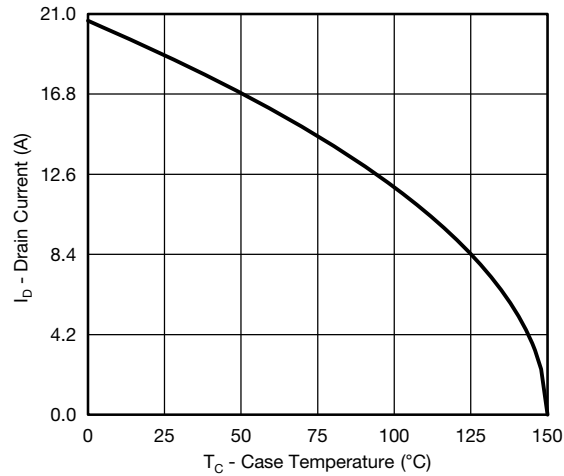
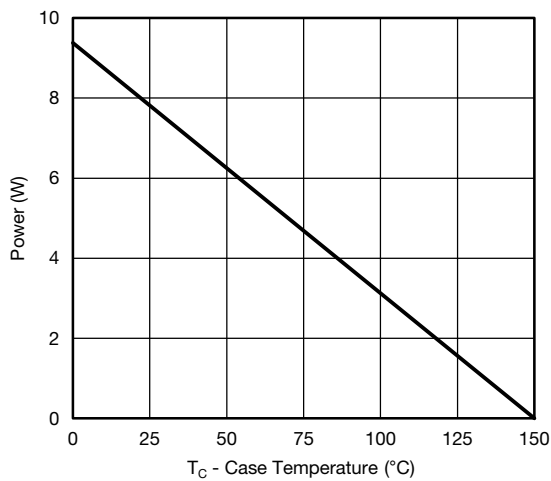
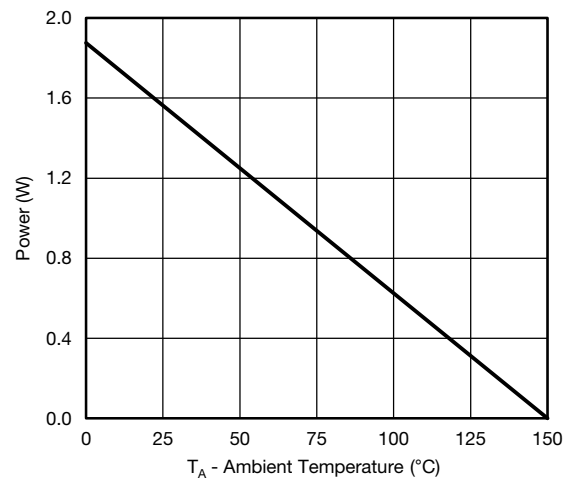
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

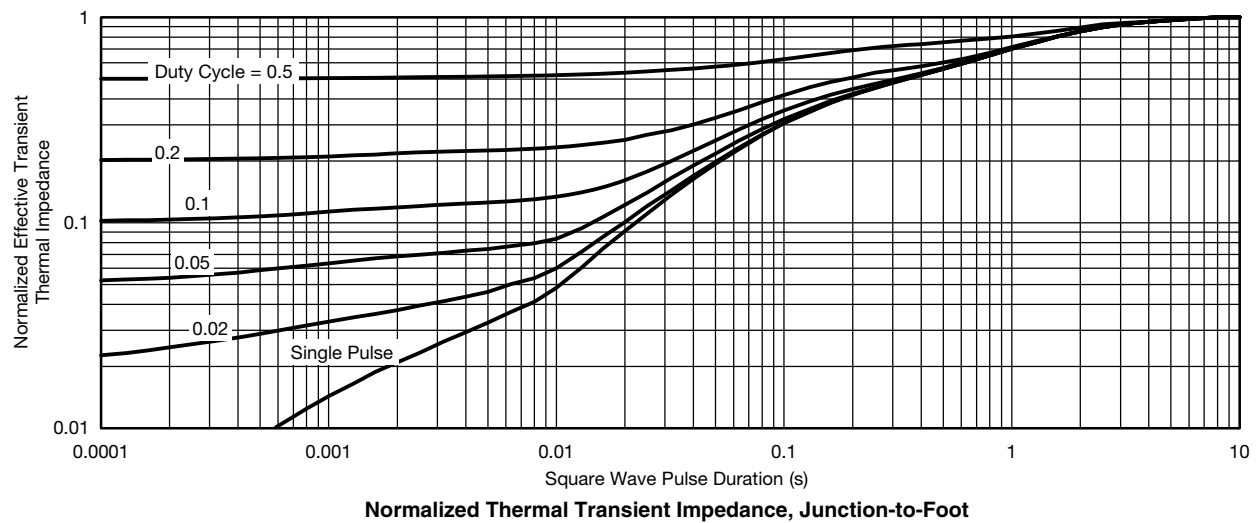
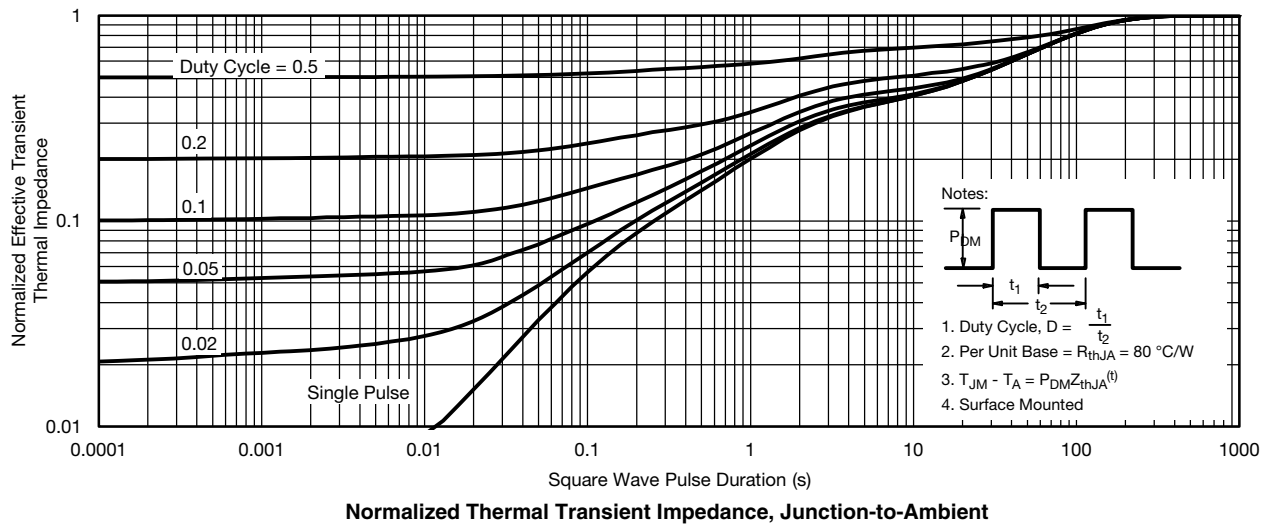
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

Safe Operating Area, Junction-to-Ambient

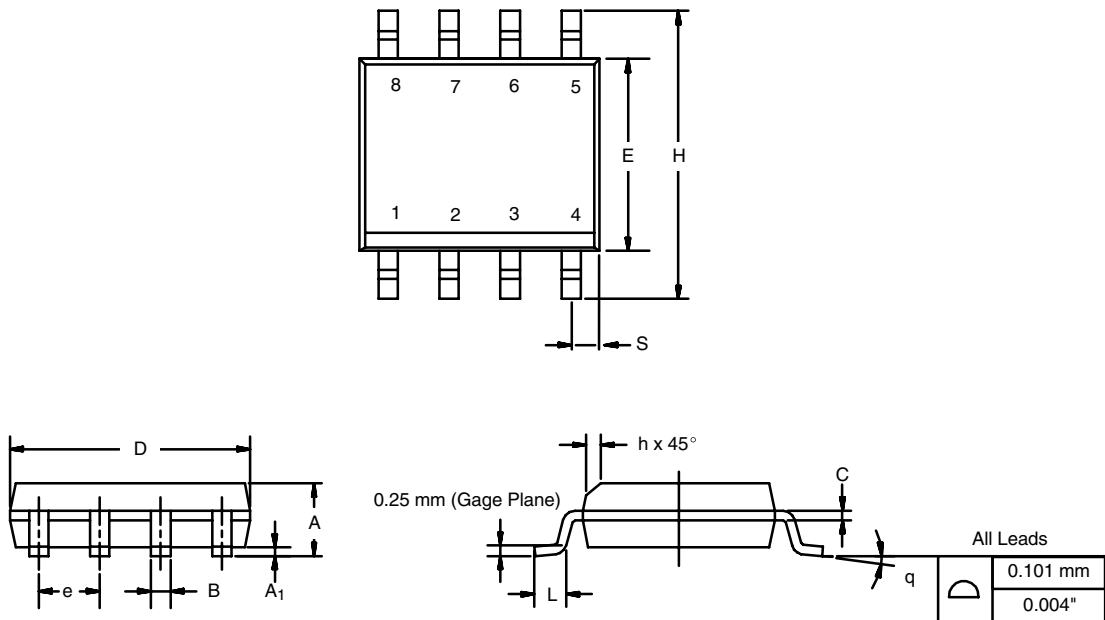
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Foot

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

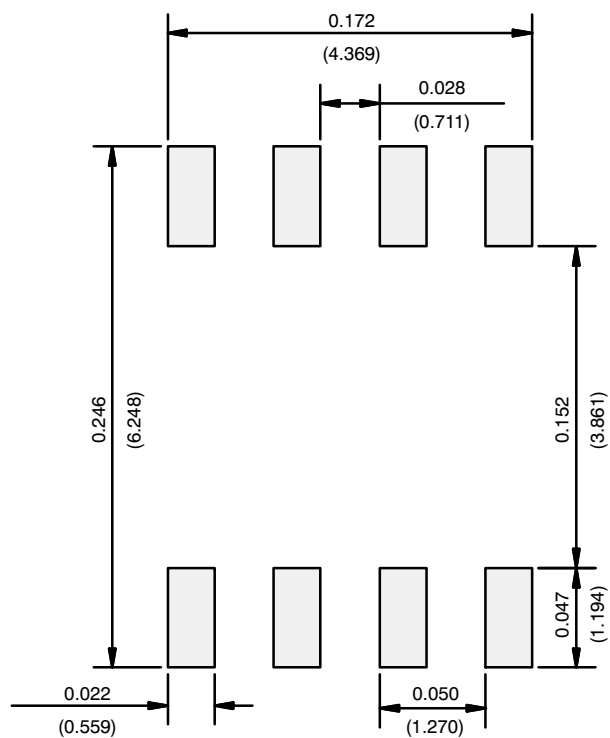
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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